Triacs logic level

BT136S series D

BT136M series D

## **GENERAL DESCRIPTION**

# Glass passivated, sensitive gate triacs in a plastic envelope suitable for surface mounting, intended for use in general purpose bidirectional switching and phase control

switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

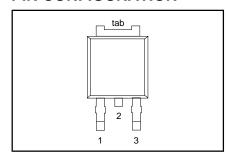
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SYMBOL	PARAMETER	MAX.	MAX.	UNIT
V <sub>DRM</sub> I <sub>T(RMS)</sub> I <sub>TSM</sub>	BT136S (or BT136M)- Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current	<b>500D</b> 500 4 25	600D 600 4 25	V A A

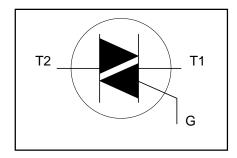
## **PINNING - SOT428**

PIN NUMBER	Standard S	Alternative M
1	MT1	gate
2	MT2	MT2
3	gate	MT1
tab	MT2	MT2

## **PIN CONFIGURATION**



## **SYMBOL**



# LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
V <sub>DRM</sub>	Repetitive peak off-state voltages		-	<b>-500</b> 500 <sup>1</sup>	<b>-600</b> 600 <sup>1</sup>	V
I <sub>T(RMS)</sub> I <sub>TSM</sub>	RMS on-state current Non-repetitive peak on-state current	full sine wave; $T_{mb} \le 107  ^{\circ}\text{C}$ full sine wave; $T_{j} = 25  ^{\circ}\text{C}$ prior to surge	-	4		А
		t = 20 ms t = 16.7 ms	-	2! 2	5	A A
l²t dl <sub>⊤</sub> /dt	I <sup>2</sup> t for fusing Repetitive rate of rise of on-state current after	t = 10.7  ms t = 10  ms $I_{TM} = 6 \text{ A}; I_{G} = 0.2 \text{ A};$ $dI_{G}/dt = 0.2 \text{ A}/\mu\text{s}$	-	3.		A <sup>2</sup> s
	triggering	T2+ G+	-	50		A/μs
		T2+ G- T2- G-	-	50 50		A/μs A/μs
		T2- G+	-	10		A/μs
I <sub>GM</sub> V <sub>GM</sub> P <sub>GM</sub>	Peak gate current Peak gate voltage Peak gate power		- - -	2 5 5	,	Ä V W
P <sub>G(AV)</sub> T <sub>stg</sub>	Average gate power Storage temperature Operating junction temperature	over any 20 ms period	- -40 -	0. 15 12	5 60	,C ,C

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<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 3 A/µs.

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# THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-mb</sub>	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle pcb (FR4) mounted; footprint as in Fig.14	-	- - 75	3.0 3.7 -	K/W K/W K/W

# STATIC CHARACTERISTICS

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
I <sub>GT</sub>	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$					
			Γ2+ G+	-	2.0	5	mΑ
		1	Γ2+ G-	-	2.5	5 5	mΑ
		1	Γ2- G-	-	2.5	5	mΑ
			Γ2- G+	-	5.0	10	mΑ
I <sub>L</sub>	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$					
			Γ2+ G+	-	1.6	10	mΑ
		]	Γ2+ G-	-	4.5	15	mΑ
			Γ2- G-	-	1.2	10	mΑ
		1	Γ2- G+	-	2.2	15	mΑ
l <sub>H</sub>	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$		-	1.2	10	mΑ
$V_{T}$	On-state voltage	$I_T = 5 A$		-	1.4	1.70	V
$egin{array}{c} oldsymbol{I}_H \ oldsymbol{V}_T \ oldsymbol{V}_GT \end{array}$	Gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	_	-	0.7	1.5	V
		$ V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_i = 125 ^{\circ}\text{C}$	C	0.25	0.4	-	V
$I_D$	Off-state leakage current	$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ} \text{ V}$ $V_D = V_{DRM(max)}; T_j = 125 ^{\circ} \text{ C}$		-	0.1	0.5	mA

# **DYNAMIC CHARACTERISTICS**

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV <sub>D</sub> /dt	Critical rate of rise of	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 °C;$	-	5	-	V/μs
t <sub>gt</sub>	off-state voltage Gate controlled turn-on time	exponential waveform; $R_{GK} = 1 \text{ k}\Omega$ $I_{TM} = 6 \text{ A}$ ; $V_D = V_{DRM(max)}$ ; $I_G = 0.1 \text{ A}$ ; $dI_G/dt = 5 \text{ A}/\mu s$	-	2	-	μs

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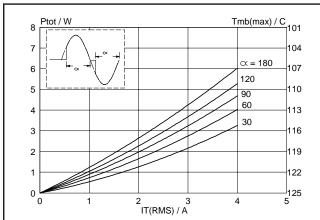


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha =$  conduction angle.

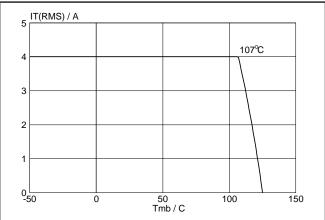


Fig.4. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

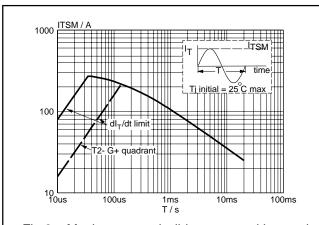


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \le 20$ ms.

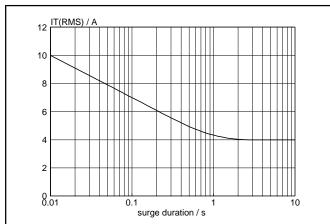


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{mb} \le 107$  °C.

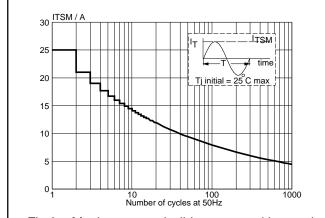


Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents, f = 50 Hz.

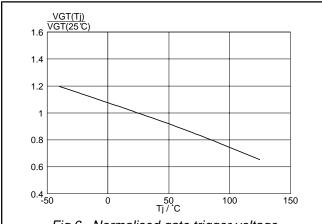
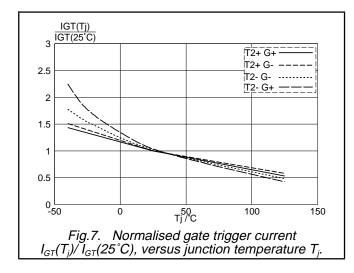


Fig.6. Normalised gate trigger voltage  $V_{GT}(T_j)/V_{GT}(25\,^{\circ}C)$ , versus junction temperature  $T_j$ .

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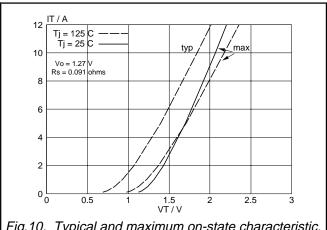
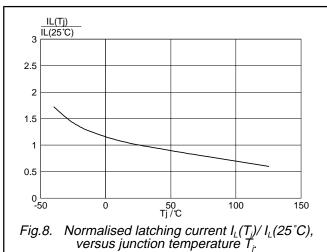
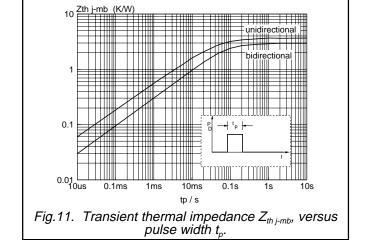
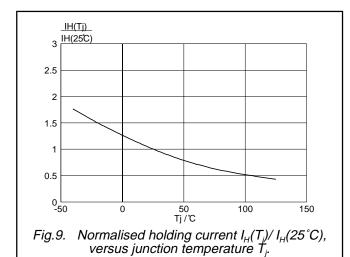


Fig. 10. Typical and maximum on-state characteristic.







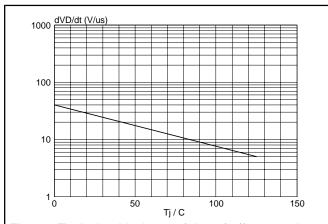
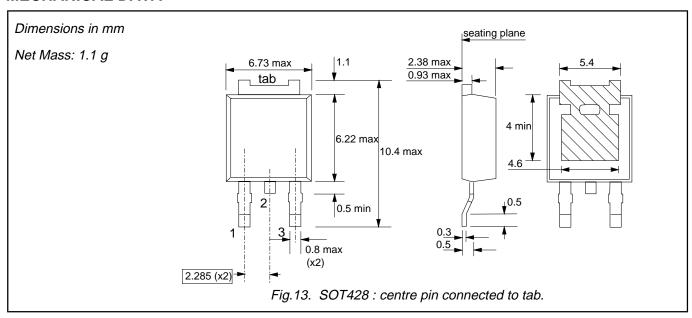


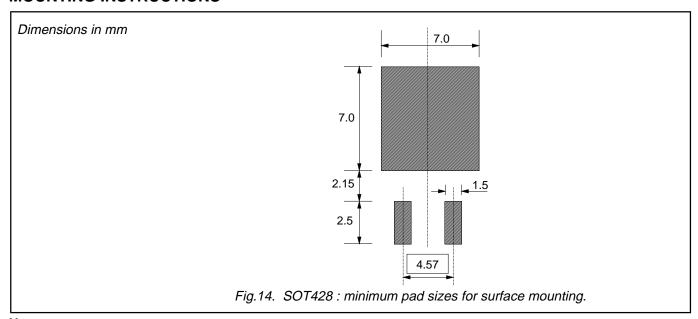
Fig.12. Typical, critical rate of rise of off-state voltage,  $d\dot{V}_D/dt$  versus junction temperature  $T_i$ .

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# **MECHANICAL DATA**



# **MOUNTING INSTRUCTIONS**



## **Notes**

1. Plastic meets UL94 V0 at 1/8".

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## **DEFINITIONS**

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.

## Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

## **Application information**

Where application information is given, it is advisory and does not form part of the specification.

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